NII SEMI

# WD3132 High Efficiency, 38V Step-Up White LED Driver for Medium LCD Panel Backlight

# Descriptions

The WD3132 is a constant current, high efficiency LED driver. Internal MOSFET can drive up to 10 white LEDs in series and 10S4P / 8S5P LEDs with 38V OVP. Peak inductor current limit is larger than 1.5A. For LED dimming, a Pulse-Width-Modulation (PWM) signal can be applied to the EN pin. The device operates at optimized 600k Hz fixed switching frequency to reduce output ripple, improve conversion efficiency, and allows use small external components.

The WD3132 is available in SOT-23-6L package. Standard product is Pb-free and Halogen-free.

: 200mV (±5%)

: 600k Hz (Typ.)

: 1.5A (Min.)

: Min. 4%

: Up to 92% (10S4P)

: 5KHz to 200KHz

## Features

- Input voltage range : 3~5.5V
- Open LED Protection : 38V
- Reference Voltage
- Switching frequency
- Efficiency
- Main switch current limit
- PWM Dimming frequency
- PWM Dimming Duty

# Applications

- Smart Phones
- Tablets
- Portable games



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SOT-23-6L



## Pin configuration (Top view)



Marking

# **Order information**

Device	Package	Shipping
WD3132E-6/TR	SOT-23-6L	3000/Reel&Tape

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# **Typical applications**



# **Pin descriptions**

Symbol	Pin No.	Descriptions
LX	1	Switch Output
GND	2	Ground
FB	3	Feedback
EN	4	Enable, Active High
OVP	5	OVP Pin, Connect
OVP	Э	to VOUT
VIN	6	Power Supply

# **Block diagram**





# Absolute maximum ratings

Parameter	Symbol	Value	Unit
VIN pin voltage range	V <sub>IN</sub>	-0.3~6.5	V
OVP pin voltage range	V <sub>OVP</sub>	-0.3~45	V
EN pin voltage range	-	-0.3~V <sub>IN</sub>	V
LX pin voltage range (DC)	-	-0.3~45	V
Power Dissipation – SOT-23-6L (Note 1)	Б	0.5	W
Power Dissipation – SOT-23-6L (Note 2)	- P <sub>D</sub>	0.3	W
Junction to Ambient Thermal Resistance – SOT-23-6L (Note 1)	Р	250	°C/W
Junction to Ambient Thermal Resistance – SOT-23-6L (Note 2)	- R <sub>θJA</sub>	416	°C/W
Junction temperature	TJ	150	°C
Lead temperature(Soldering, 10s)	TL	260	°C
Operation temperature	Topr	-40 ~ 85	°C
Storage temperature	Tstg	-55 ~ 150	°C

These are stress ratings only. Stresses exceeding the range specified under "Absolute Maximum Ratings" may cause substantial damage to the device. Functional operation of this device at other conditions beyond those listed in the specification is not implied and prolonged exposure to extreme conditions may affect device reliability.

**Note 1:** Surface mounted on FR-4 board using 1 square inch pad size, dual side, 1oz copper **Note 2:** Surface mounted on FR-4 board using minimum pad size, 1oz copper



# **Electrical Characteristics**

(Ta=25°C, V<sub>IN</sub>=3.6V, V<sub>EN</sub>=V<sub>IN</sub>, C<sub>IN</sub>=4.7uF, C<sub>OUT</sub>=2.2uF, unless otherwise noted.)

Parameter	Symbol	<b>Test Condition</b>	Min	Тур	Мах	Units
Operation Voltage Range	V <sub>IN</sub>		3		5.5	V
Under Voltage Lockout	V <sub>UVLO</sub>	V <sub>IN</sub> Rising	1.8	2.2	2.5	V
UVLO Hysteresis	V <sub>UVLO-HYS</sub>			0.1		V
Over-Voltage Threshold	V <sub>OVP</sub>		36	38	40	V
Quiescent Current	Ι <sub>Q</sub>	No Switching		0.3	1	mA
Supply Current	Is	Switching		1.5	3	mA
Shutdown Current	I <sub>SD</sub>	$V_{EN} < 0.4V$			1	μA
Operation Frequency	f <sub>osc</sub>		500	600	700	kHz
Maximum Duty Cycle	D <sub>MAX</sub>		92			%
PWM Dimming Clock Rate		Recommended	5		200	KHz
Feedback Reference	$V_{REF}$		190	200	210	mV
On Resistance	R <sub>ON</sub>	I <sub>LX</sub> =100mA		0.3		Ω
Current Limit	I <sub>LIM</sub>		1.5			А
EN Threshold Voltage	V <sub>ENL</sub>				0.4	V
	V <sub>ENH</sub>		1.5			V
EN Sink Current	I <sub>EN</sub>			3		μA
Thermal Shutdown Temperature	T <sub>SD</sub>			160		°C
T <sub>SD</sub> Hysteresis	T <sub>SD-HYS</sub>			30		°C
Shutdown Delay	t <sub>SHDN</sub>			1		ms



## Typical Characteristics (Ta=25°C, unless otherwise noted)



Efficiency vs. Output Current



Efficiency vs. Output Current



Efficiency vs. Output Current



LED Current vs. Supply Voltage



Efficiency vs. Output Current



LED Current vs. Temperature



WD3132



LED Current vs. PWM Duty



LED Current vs. PWM Duty



Enable Threshold Voltage vs. Supply Voltage



Frequency vs. Supply Voltage



**Quiescent Current vs. Supply Voltage** 



Frequency vs. Temperature





LED Open Shut-Down from VIN

LED Open Start-Up from VIN

# **Operation Information**

#### **Normal Operation**

The WD3132 is a high efficiency, high output voltage boost converter. The device is ideal for driving white LEDs. The LED connection provides even illumination by sourcing the same output current through all LEDs. The device switches FET and operates in pulse width modulation (PWM) with 600 kHz fixed switching frequency. The beginning of each cycle turns on the Power MOSFET. A slope compensation ramp is added to the current sense amplifier and the result is fed into the positive input of the comparator (COMP). When this voltage goes above the output voltage of the error amplifier (EA), the Power MOSFET is turned off. The FB voltage can be regulated to the high precision reference voltage with EA block. A low reference voltage (200mV typical), reduces the power dissipation on the current sense resistor.

#### Soft-Start

The WD3132 Build-in Soft-Start function limits the inrush current while the device turn-on.

#### Cycle-by-Cycle Current Limit

The WD3132 uses a cycle-by-cycle current limit circuitry to limit the inductor peak current in the event of an overload condition. The current flow through inductor in charging phase is detected by a current sensing circuit. As the value comes across the current limiting threshold, the N- MOSFET turns off, so that the inductor will be forced to leave charging stage and enter in discharging stage. Therefore, the inductor current will not increase over the current limiting threshold.

#### **Over-Voltage-Protection (OVP)**

The Over Voltage Protection is detected by OVP block, prevents IC damage as the result of white LED disconnection.

Once output voltage goes over the OVP threshold,

LX pin stops switching and the N-MOSFET will be turned off. Then, the output voltage will be clamped to a voltage near OVP threshold. Until the OVP eliminates the N-MOSFET will be turned on.

#### **UVLO Protection**

To avoid malfunction of the WD3132 at low input voltages, an under voltage lockout is included that disables the device, until the input voltage exceeds 2.2V (Typ.).

#### Shutdown Mode

Drive EN to GND to place the WD3132 in shutdown mode. In shutdown mode, the reference, control circuits, and the main switch turn off. Input current falls to smaller than  $1\mu$ A during shutdown mode.

#### **Over-Temperature-Protection (OTP)**

As soon as the junction temperature  $(T_J)$  exceeds  $160^{\circ}C$  (Typ.), the WD3132 goes into thermal shutdown. In this mode, the main N-MOSFET is turned off until temperature falls below typically  $130^{\circ}C$ . Then the device starts switching again.



### **Application Information**

External component selection for the application circuit depends on the load current requirements. Certain trade-offs between different performance parameters can also be made.

#### **LED Current Setting**

The loop of Boost structure will keep the FB pin voltage equal to the reference voltage  $V_{REF}$ . Therefore, when  $R_{SET}$  connects FB pin and GND, the current flows from  $V_{OUT}$  through LED and  $R_{SET}$  to GND will be set by the current on  $R_{SET}$ , which is equal to following equation:

$$I_{\text{LED}} = \frac{V_{\text{FB}}}{R_{\text{SET}}} = \frac{200 \text{mV}}{R_{\text{SET}}}$$

Where

 $I_{LED}$  = output current of LEDs

 $V_{FB}$  = regulated voltage of FB

R<sub>SET</sub> = current sense resistor

The output current tolerance depends on the FB accuracy and the current sensor resistor accuracy.

#### **Dimming Control**

For the brightness dimming control of the WD3132, the IC provides typically 200mV feedback voltage when the EN pin is pulled constantly high. However, EN pin allows a PWM signal to reduce this regulation voltage by changing the PWM duty cycle to achieve LED brightness dimming control.

As shown in Figure 1, the duty cycle of the PWM signal is used to chop the internal 200mV reference voltage. An internal low pass filter is used to filter the pulse signal. And then the reference voltage can be made by connecting the output of the filter to the error amplifier for the FB pin voltage regulation.



#### Figure1

Therefore, although a PWM signal is applied for dimming, but only the WLED DC current is modulated. This helps to eliminate the audible noise which often occurs when the LED current is pulsed in replica of the frequency and the duty cycle of PWM control. The minimum dimming frequency is limited by EN shutdown delay time. For optimum performance, recommend to select PWM dimming frequency in the range of 5kHz~200kHz, and dimming duty > 4%.

$$I_{LED} = \frac{V_{FB} \times D}{R_{SET}} = \frac{200 \text{mV} \times D}{R_{SET}}$$

Where

D = PWM Dimming Duty, from 4% to 100%

The EN shutdown delay time is set to 1ms. This means the IC will shutdown if EN keeps low for 1ms.

#### Applications for Driving 10S4P LEDs

The WD3132 can drive different WLEDs topology. For example, the following figure shows the 10S4P WLEDs and output current equals to 80mA. The total WLEDs current can be set by the RSET.

For driving 10S4P total 40 LEDs panel, large power dissipation should be considered in PCB Layout Design, with large ground copper area and enough thermal via holes, etc. The total conversion efficiency also must be optimized with small DRC Inductor and fast-switching Schottky Diode. To enhance performance of driving 10S4P LEDs, VIN no less than 3.4V is recommended.



#### **Boost Inductor Selection**

The selection of the inductor affects steady state operation as well as transient behavior and loop stability. Inductor values can have ±20% tolerance with no current bias. When the inductor current approaches saturation level, its inductance can decrease 20% to 35% from the 0A value depending on how the inductor vendor defines saturation current. Using an inductor with a smaller inductance value forces discontinuous PWM when the inductor current ramps down to zero before the end of each switching cycle. This reduces the boost converter's maximum output current, causes large input voltage ripple and reduces efficiency. Large inductance value provides much more output current and higher conversion efficiency. The inductor should have low core loss at 600k Hz and low DCR for better efficiency. For these reasons, the recommended value of inductor for 10S4P/8S5P LEDs applications is  $10\mu$ H to  $22\mu$ H. A  $10\mu$ H inductor optimized the efficiency for most application while maintaining low inductor peak to peak ripple, low DCR and large saturation current.

#### **Input Capacitor Selection**

Connect the input capacitance from V<sub>IN</sub> to the reference ground plane. Input capacitance reduces the ac voltage ripple on the input rail by providing a low-impedance path for the switching current of the boost converter. The capacitor in the range of  $4.7\mu$ F to  $10\mu$ F / X7R or X5R is recommended for input side.

#### **Output Capacitor Selection**

The output capacitor is mainly selected to meet the requirements for the output ripple and loop stability. This ripple voltage is related to the capacitor's capacitance and its equivalent series resistance (ESR). A minimum 2.2 $\mu$ F X5R or X7R ceramic capacitor at output is recommended for 10S4P LEDs applications referred to *Typical Application Circuits* on Page 12. And sufficient high voltage capacitor should be carefully used here.

#### **Diode Selection**

The rectifier diode supplies current path to the inductor when the internal MOSFET is off. Use a Schottky with low forward voltage to reduce losses. The diode should be rated for a reverse blocking voltage greater than the output voltage used. The average current rating must be greater than the maximum load current expected, and the peak current rating must be greater than the peak inductor current.

Diode following requirements:

- Low forward voltage
- High switching speed : 50ns max.
  - Reverse voltage : V<sub>OUT</sub> + V<sub>F</sub> or more
- Rated current : I<sub>PK</sub> or more



#### **PCB Layout Considerations**

A good circuit board layout aids in extracting the most performance from the WD3132. Poor circuit layout degrades the output ripple and the electromagnetic interference (EMI) or electromagnetic compatibility (EMC) performance. The evaluation board layout is optimized for the WD3132. Use this layout for best performance. If this layout needs changing, use the following guidelines:

- 1. Use separate analog and power ground planes. Connect the sensitive analog circuitry (such as voltage divider components) to analog ground; connect the power components (such as input and output bypass capacitors) to power ground. Connect the two ground planes together near the load to reduce the effects of voltage dropped on circuit board traces. Locate  $C_{IN}$  as close to the  $V_{IN}$  pin as possible, and use separate input bypass capacitors for the analog.
- 2. Route the high current path from  $C_{IN}$ , through L to the LX and GND pins as short as possible.
- 3. Keep high current traces as short and wide as possible.
- The output filter of the boost converter is also critical for layout. The Diode and Output capacitors should be placed to minimize the area of current loop through Output –GND–LX.
- 5. Avoid routing high impedance traces, such as Output, near the high current traces and components or near the Diode node.
- 6. If high impedance traces are routed near high current and/or the LX node, place a ground plane shield between the traces.
- Place the R<sub>SET</sub> resistor as close as possible to FB pin, for the FB is a high impedance input pin which is susceptible to noise.



WD3132 PCB Suggest Layout (Demo)



### **Typical applications Circuits**



1. Multiple Strings of 3-Series LED Load

#### **Recommendation:**

L1:  $10\mu$ H~22 $\mu$ H, saturation current > 1.5A



2. Multiple Strings of 8-Series LED Load

#### **Recommendation:**

L1: 10µH~22µH, saturation current > 1.5A



3. Multiple Strings of 10-Series LED Load

#### **Recommendation:**

L1:  $10\mu$ H~22 $\mu$ H, saturation current > 1.5A



WD3132









Symbol	Dimensions in millimeter			
	Min.	Тур.	Max.	
A	1.050	-	1.250	
A1	0.000	-	0.100	
A2	1.050	-	1.150	
b	0.300	-	0.500	
С	0.100	-	0.200	
D	2.820	2.900	3.020	
E	1.500	1.600	1.700	
E1	2.650	2.800	2.950	
е	0.950(BSC)			
e1	1.800	-	2.000	
L	0.300	-	0.600	
θ	0°	-	8°	

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